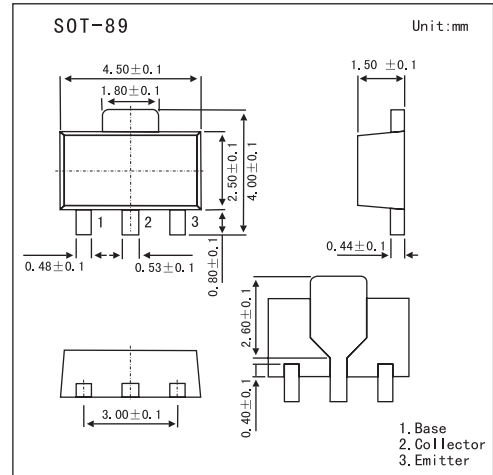


2SA1735

■ Features

- Low Saturation Voltage: $V_{CE(sat)} = -0.5V$ (max) ($I_C = -500mA$)
- High Speed Switching Time: $t_{stg} = 0.25\mu s$ (typ.)
- Small Flat Package
- $P_C = 1$ to $2W$ (mounted on ceramic substrate)
- Complementary to 2SC4540



■ Absolute Maximum Ratings $T_a = 25^\circ C$

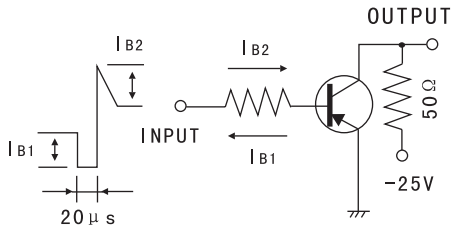
Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-6	V
Collector Current	I_C	-1	A
Base Current	I_B	-0.2	A
Collector Power Dissipation	P_C	500	mW
	P_C^*	1000	
Junction temperature	T_j	150	$^\circ C$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ C$

* Mounted on ceramic substrate ($250\text{ mm}^2 \times 0.8\text{ t}$)

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB} = -60V, I_E = 0$			-0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -6V, I_C = 0$			-0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-50			V
DC Current Gain	h_{FE}	$V_{CE} = -2V, I_C = -100mA$	120		400	
		$V_{CE} = -2V, I_C = -700mA$	40			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -25mA$			-0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -25mA$			-1.2	V
Transition Frequency	f_T	$V_{CE} = -2V, I_C = -100mA$		100		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		16		pF
Turn-On Time	t_{on}	See Test Circuit.		0.1		μs
Storage Time	t_{stg}			0.25		
Fall Time	t_f			0.1		

■ Test Circuit



$-I_{B1} = I_{B2} = 25\text{mA}$, DUTY CYCLE $\leq 1\%$

■ Marking

Marking	LC
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■ Electrical Characteristics Curves

